TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK1530

High Power Amplifier Application

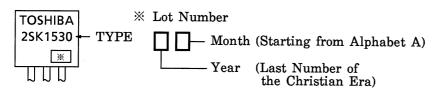
Unit: mm

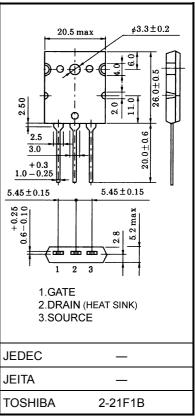
• Complementary to 2SJ201

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	V_{DSS}	200	V	
Gate-source voltage	V _{GSS}	±20	V	
Drain current (Note 1)	I _D	12	Α	
Drain power dissipation (Tc = 25°C)	P_{D}	150	W	
Channel temperature	T _c	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	

Marking





Weight: 9.75 g (typ.)

Electrical Characteristics (Ta = 25°C)

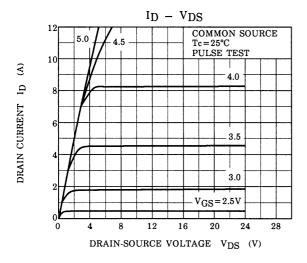
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0	_	_	1.0	mA
Gate leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20 V	_	_	±0.5	μA
Drain-source breakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0	200	_	_	V
Drain-source saturation voltage	V _{DS (ON)}	I _D = 8 A, V _{GS} = 10 V	_	2.5	5.0	V
Gate-source cut-off voltage (Note 2)	V _{GS (OFF)}	V _{DS} = 10 V, I _D = 0.1 A	0.8	_	2.8	٧
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 5 A		5.0	_	S
Input capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0, f = 1 MHz	-	900	_	
Output capacitance	C _{oss}	V _{DS} = 30 V, V _{GS} = 0, f = 1 MHz	_	180	_	pF
Reverse transfer capacitance	C _{rss}	V _{DD} = 30 V, V _{GS} = 0, f = 1 MHz	_	100	_	

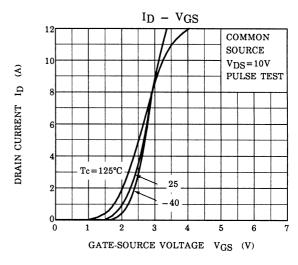
Note 1: Please use devices on condition that the channel temperature is below 150°C.

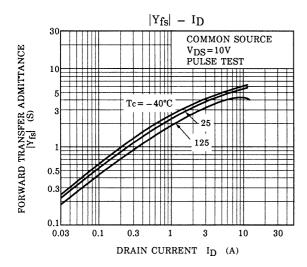
Note 2: V_{GS (OFF)} Classification 0: 0.8~1.6 Y: 1.4~2.8

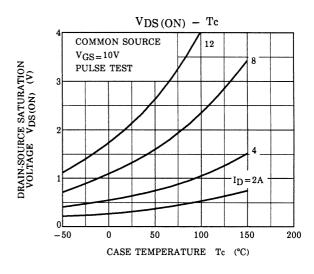
This transistor is an electrostatic sensitive device.

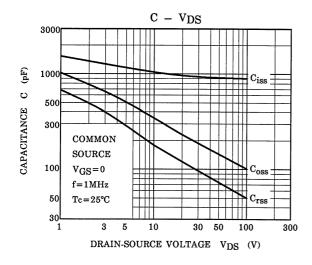
Please handle with caution.

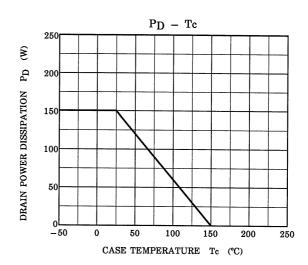




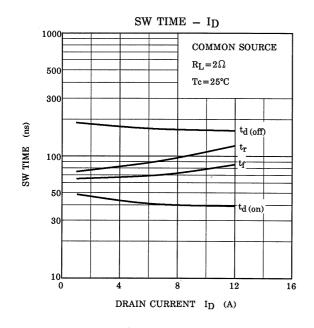


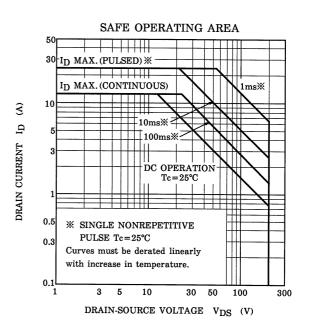




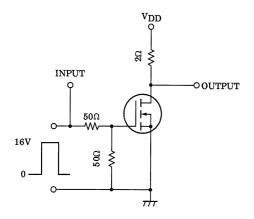


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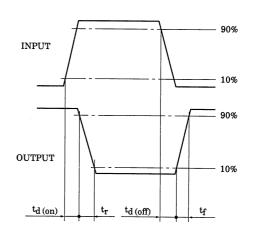


Switching Time Test Circuit



Waveforms

3



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